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Sut	ostitute for form 1449/PTC	,		Application Number	10/537,804	
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	TATEMENT			First Named Inventor	Robert DWILINSKI	
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	(Use as many s	sheets as ne	ecessary)	Examiner Name	F. C. Hiteshew	
Sheet	1	of	2	Attorney Docket Number	204552035400	

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Examiner	Date	
Signature	Considered	

^{*}EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁵ Applicant is to place a check mark here if English language Translation is attached.

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Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²			
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(Use as many sheets as necessary)			s necessary)	Examiner Name	F. C. Hiteshew	
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Examiner Signature /Matthew Song/	Date Considered	06/04/2010
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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